

IN THE CLAIMS:

Please cancel claims 4 and 9 in their entirety without prejudice nor disclaimer of the subject matter set forth therein.

Please amend claims 1-3, 5-8 and 10 as follows:

1. (Currently Amended) A semiconductor memory device comprising a memory cell capacitor for storing data thereon, the capacitor being made up of a ~~first electrode~~ lower electrode connected to a contact plug,

~~a second electrode~~ an upper electrode and a capacitive insulating film interposed between the ~~first and second electrodes~~ lower and upper electrodes,

wherein the ~~first electrode~~ lower electrode includes a ~~first barrier film~~ first film of the lower electrode in contact with the contact plug and a ~~second barrier film~~ second film of the lower electrode, which is formed on the ~~first barrier film~~ first film of the lower electrode and prevents the diffusion of oxygen, [[and]]

wherein the ~~second barrier film~~ second film of the lower electrode covers the upper and side faces of the ~~first barrier film~~ first film of the lower electrode

wherein a thickness of the second film of the lower electrode is between 70 nm and 250 nm.

2. (Currently Amended) The memory device of Claim 1, wherein the ~~first barrier film~~ first film of the lower electrode includes a film that prevents a constituent element of the contact plug from diffusing into the capacitive insulating film.

3. (Currently Amended) The memory device of Claim 2, wherein the ~~first barrier film~~ first film of the lower electrode includes ~~a film~~ one or more films selected from the group consisting of TiN, TiAlN, TiSiN, TaN, TaSiN, ~~[[and]] TaAlN, Ti and Ta~~ films.

4. (Cancelled)

5. (Currently Amended) The memory device of Claim 2, wherein the ~~second barrier film~~ second film of the lower electrode includes an Ir or IrO₂ film.

6. (Currently Amended) A semiconductor memory device comprising a memory cell capacitor for storing data thereon, the capacitor being made up of a ~~first electrode~~ lower electrode connected to a contact plug, ~~a second electrode~~ an upper electrode and a capacitive insulating film interposed between the ~~first and second electrodes~~ lower and upper electrodes, wherein the ~~first electrode~~ lower electrode includes a ~~first barrier film~~ first film of the lower electrode in contact with the contact plug, a ~~second barrier film~~ second film of the lower electrode covering the upper surface of the ~~first barrier film~~ first film of the lower electrode and a ~~third barrier film~~ third film of the lower electrode covering the side faces of the ~~first barrier film~~ first film of the lower electrode, ~~[[and]]~~

wherein the ~~second and third barrier films~~ second and third films of the lower electrode prevent the diffusion of oxygen, and

wherein a thickness of the second film of the lower electrode is between 70 nm and 250 nm.

7. (Currently Amended) The memory device of Claim 6, wherein the ~~first barrier film~~ first film of the lower electrode includes a film that prevents a constituent element of the contact plug from diffusing into the capacitive insulating film.

8. (Currently Amended) The memory device of Claim 7, wherein the ~~first barrier film~~ first film of the lower electrode includes ~~a film~~ one or more films selected from the group consisting of TiN, TiAlN, TiSiN, TaN, TaSiN, ~~[[and]] TaAlN,~~ Ti and Ta films.

9. (Cancelled)

10. (Currently Amended) The memory device of Claim 7, wherein each of the ~~second and third barrier films~~ second and third films of the lower electrode includes an Ir or IrO₂ film.